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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, EBI/EMI, I²C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	52
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4a6rgt7tr

3.4 Embedded Flash memory

STM32L4A6xG devices feature 1 Mbyte of embedded Flash memory available for storing programs and data. The Flash memory is divided into two banks allowing read-while-write operations. This feature allows to perform a read operation from one bank while an erase or program operation is performed to the other bank. The dual bank boot is also supported. Each bank contains 256 pages of 2 Kbyte.

Flexible protections can be configured thanks to option bytes:

- Readout protection (RDP) to protect the whole memory. Three levels are available:
  - Level 0: no readout protection
  - Level 1: memory readout protection: the Flash memory cannot be read from or written to if either debug features are connected, boot in RAM or bootloader is selected
  - Level 2: chip readout protection: debug features (Cortex-M4 JTAG and serial wire), boot in RAM and bootloader selection are disabled (JTAG fuse). This selection is irreversible.

Table 3. Access status versus readout protection level and execution modes

Area	Protection level	User execution			Debug, boot from RAM or boot from system memory (loader)		
		Read	Write	Erase	Read	Write	Erase
Main memory	1	Yes	Yes	Yes	No	No	No
	2	Yes	Yes	Yes	N/A	N/A	N/A
System memory	1	Yes	No	No	Yes	No	No
	2	Yes	No	No	N/A	N/A	N/A
Option bytes	1	Yes	Yes	Yes	Yes	Yes	Yes
	2	Yes	No	No	N/A	N/A	N/A
Backup registers	1	Yes	Yes	N/A(1)	No	No	N/A(1)
	2	Yes	Yes	N/A	N/A	N/A	N/A
SRAM2	1	Yes	Yes	Yes(1)	No	No	No(1)
	2	Yes	Yes	Yes	N/A	N/A	N/A

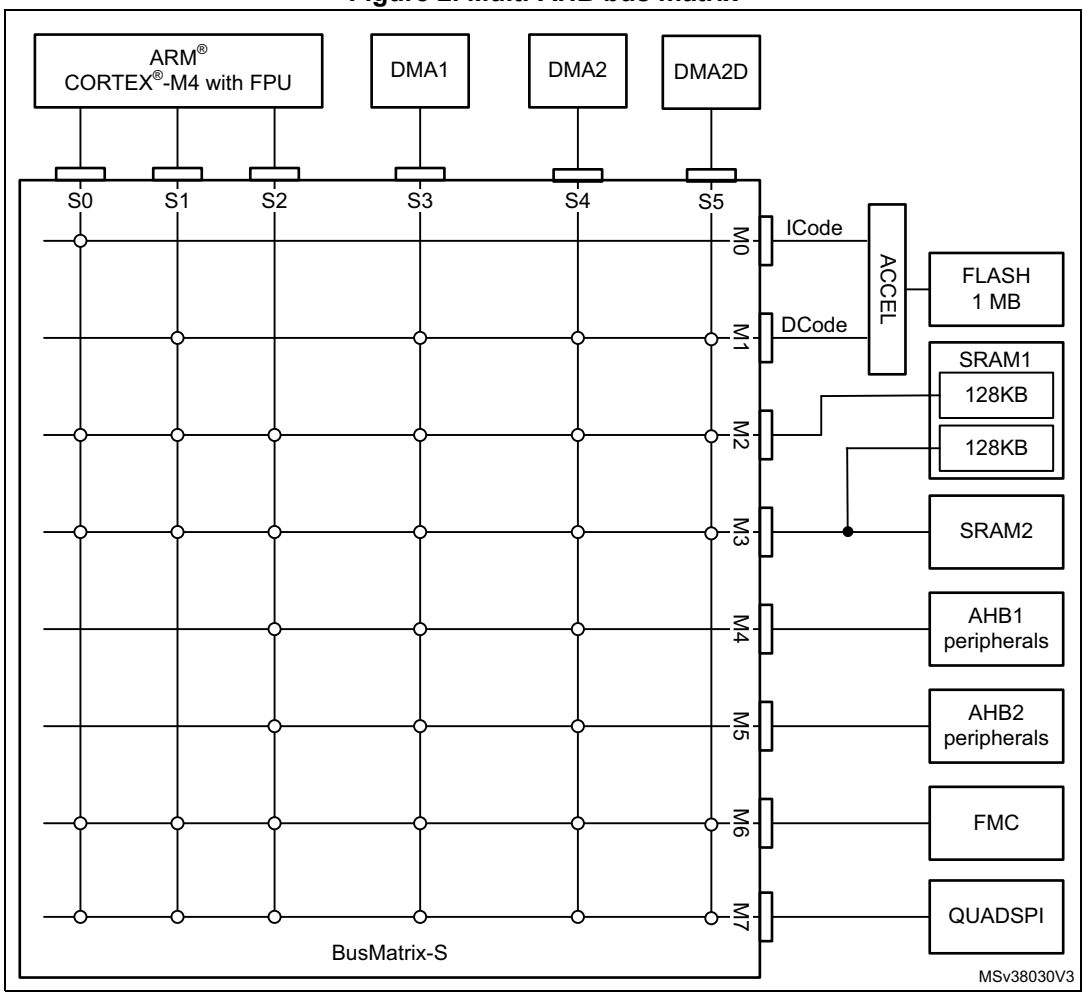
1. Erased when RDP change from Level 1 to Level 0.

- Write protection (WRP): the protected area is protected against erasing and programming. Two areas per bank can be selected, with 2-Kbyte granularity.
- Proprietary code readout protection (PCROP): a part of the flash memory can be protected against read and write from third parties. The protected area is execute-only: it can only be reached by the STM32 CPU, as an instruction code, while all other accesses (DMA, debug and CPU data read, write and erase) are strictly prohibited. One area per bank can be selected, with 64-bit granularity. An additional option bit (PCROP_RDP) allows to select if the PCROP area is erased or not when the RDP protection is changed from Level 1 to Level 0.

3.6 Multi-AHB bus matrix

The 32-bit multi-AHB bus matrix interconnects all the masters (CPU, DMAs and the DMA2D) and the slaves (Flash memory, RAM, FMC, QUADSPI, AHB and APB peripherals) and ensures a seamless and efficient operation even when several high speed peripherals work simultaneously.

Figure 2. Multi-AHB bus matrix



3.7 Firewall

The device embeds a Firewall which protects code sensitive and secure data from any access performed by a code executed outside of the protected areas.

Each illegal access generates a reset which kills immediately the detected intrusion.

By default, the microcontroller is in Run mode after a system or a power Reset. It is up to the user to select one of the low-power modes described below:

- **Sleep** mode

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Low-power run** mode

  This mode is achieved with V_{CORE} supplied by the low-power regulator to minimize the regulator's operating current. The code can be executed from SRAM or from Flash, and the CPU frequency is limited to 2 MHz. The peripherals with independent clock can be clocked by HSI16.

- **Low-power sleep** mode

  This mode is entered from the low-power run mode. Only the CPU clock is stopped. When wakeup is triggered by an event or an interrupt, the system reverts to the low-power run mode.

- **Stop 0, Stop 1 and Stop 2** modes

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the V_{CORE} domain are stopped, the PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are disabled. The LSE or LSI is still running.

  The RTC can remain active (Stop mode with RTC, Stop mode without RTC).

  Some peripherals with wakeup capability can enable the HSI16 RC during Stop mode to detect their wakeup condition.

  Three Stop modes are available: Stop 0, Stop 1 and Stop 2 modes. In Stop 2 mode, most of the V_{CORE} domain is put in a lower leakage mode.

  Stop 1 offers the largest number of active peripherals and wakeup sources, a smaller wakeup time but a higher consumption than Stop 2. In Stop 0 mode, the main regulator remains ON, allowing a very fast wakeup time but with much higher consumption.

  The system clock when exiting from Stop 0, Stop 1 or Stop 2 modes can be either MSI up to 48 MHz or HSI16, depending on software configuration.

- **Standby** mode

  The Standby mode is used to achieve the lowest power consumption with BOR. The internal regulator is switched off so that the V_{CORE} domain is powered off. The PLL, the MSI RC, the HSI16 RC and the HSE crystal oscillators are also switched off.

  The RTC can remain active (Standby mode with RTC, Standby mode without RTC).

  The brown-out reset (BOR) always remains active in Standby mode.

  The state of each I/O during standby mode can be selected by software: I/O with internal pull-up, internal pull-down or floating.

  After entering Standby mode, SRAM1 and register contents are lost except for registers in the Backup domain and Standby circuitry. Optionally, SRAM2 can be retained in Standby mode, supplied by the low-power Regulator (Standby with SRAM2 retention mode).

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, WKUP pin event (configurable rising or falling edge), or an RTC event occurs (alarm, periodic wakeup, timestamp, tamper) or a failure is detected on LSE (CSS on LSE).

  The system clock after wakeup is MSI up to 8 MHz.

3.32 Universal synchronous/asynchronous receiver transmitter (USART)

The STM32L4A6xG devices have three embedded universal synchronous receiver transmitters (USART1, USART2 and USART3) and two universal asynchronous receiver transmitters (UART4, UART5).

These interfaces provide asynchronous communication, IrDA SIR ENDEC support, multiprocessor communication mode, single-wire half-duplex communication mode and have LIN Master/Slave capability. They provide hardware management of the CTS and RTS signals, and RS485 Driver Enable. They are able to communicate at speeds of up to 10Mbit/s.

USART1, USART2 and USART3 also provide Smart Card mode (ISO 7816 compliant) and SPI-like communication capability.

All USART have a clock domain independent from the CPU clock, allowing the USARTx (x=1,2,3,4,5) to wake up the MCU from Stop mode using baudrates up to 204 Kbaud. The wake up events from Stop mode are programmable and can be:

- Start bit detection
- Any received data frame
- A specific programmed data frame

All USART interfaces can be served by the DMA controller.

Table 12. STM32L4A6xG USART/UART/LPUART features

USART modes/features(1)	USART1	USART2	USART3	UART4	UART5	LPUART1
Hardware flow control for modem	X	X	X	X	X	X
Continuous communication using DMA	X	X	X	X	X	X
Multiprocessor communication	X	X	X	X	X	X
Synchronous mode	X	X	X	-	-	-
Smartcard mode	X	X	X	-	-	-
Single-wire half-duplex communication	X	X	X	X	X	X
IrDA SIR ENDEC block	X	X	X	X	X	-
LIN mode	X	X	X	X	X	-
Dual clock domain	X	X	X	X	X	X
Wakeup from Stop 0 / Stop 1 modes	X	X	X	X	X	X
Wakeup from Stop 2 mode	-	-	-	-	-	X
Receiver timeout interrupt	X	X	X	X	X	-
Modbus communication	X	X	X	X	X	-
Auto baud rate detection	X (4 modes)					-
Driver Enable	X	X	X	X	X	X
LPUART/USART data length	7, 8 and 9 bits					

1. X = supported.

Table 14. Legend/abbreviations used in the pinout table

Name		Abbreviation	Definition
Pin name		Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type		S	Supply pin
		I	Input only pin
		I/O	Input / output pin
I/O structure		FT	5 V tolerant I/O
		TT	3.6 V tolerant I/O
		RST	Bidirectional reset pin with embedded weak pull-up resistor
		Option for TT or FT I/Os	
		_f (1)	I/O, Fm+ capable
		_l (2)	I/O, with LCD function supplied by V_{LCD}
		_u (3)	I/O, with USB function supplied by V_{DDUSB}
		_a (4)	I/O, with Analog switch function supplied by V_{DDA}
		_s (5)	I/O supplied only by V_{DDIO2}
Notes		Unless otherwise specified by a note, all I/Os are set as analog inputs during and after reset.	
Pin functions	Alternate functions	Functions selected through GPIOx_AFR registers	
	Additional functions	Functions directly selected/enabled through peripheral registers	

1. The related I/O structures in *Table 15* are: FT_f, FT_fa, FT_fl, FT_fla.
2. The related I/O structures in *Table 15* are: FT_l, FT_fl, FT_lu.
3. The related I/O structures in *Table 15* are: FT_u, FT_lu.
4. The related I/O structures in *Table 15* are: FT_a, FT_la, FT_fa, FT_fla, TT_a, TT_la.
5. The related I/O structures in *Table 15* are: FT_s, FT_fs.

Table 15. STM32L4A6xG pin definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
4	E10	D9	9	E1	E1	9	9	G1	G1	PC15-OSC32_OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_OUT
-	-	-	-	D6	D6	10	10	F5	F5	PF0	I/O	FT_f	-	I2C2_SDA, FMC_A0, EVENTOUT	-
-	-	-	-	D5	D5	11	11	F4	F4	PF1	I/O	FT_f	-	I2C2_SCL, FMC_A1, EVENTOUT	-
-	-	-	-	D4	D4	12	12	F3	F3	PF2	I/O	FT	-	I2C2_SMBA, FMC_A2, EVENTOUT	-
-	-	-	-	E4	E4	13	13	G3	G3	PF3	I/O	FT_a	-	FMC_A3, EVENTOUT	ADC3_IN6
-	-	-	-	F3	F3	14	14	G4	G4	PF4	I/O	FT_a	-	FMC_A4, EVENTOUT	ADC3_IN7
-	-	-	-	F4	F4	15	15	G5	G5	PF5	I/O	FT_a	-	FMC_A5, EVENTOUT	ADC3_IN8
-	D9	E10	10	F2	F2	16	16	F2	F2	VSS	S	-	-	-	-
-	E9	E9	11	G2	G2	17	17	G2	G2	VDD	S	-	-	-	-
-	-	-	-	-	-	18	18	-	-	PF6	I/O	FT_a	-	TIM5_ETR, TIM5_CH1, QUADSPI_BK1_IO3, SAI1_SD_B, EVENTOUT	ADC3_IN9
-	-	-	-	-	-	19	19	-	-	PF7	I/O	FT_a	-	TIM5_CH2, QUADSPI_BK1_IO2, SAI1_MCLK_B, EVENTOUT	ADC3_IN10
-	-	-	-	-	-	20	20	-	-	PF8	I/O	FT_a	-	TIM5_CH3, QUADSPI_BK1_IO0, SAI1_SCK_B, EVENTOUT	ADC3_IN11

Table 15. STM32L4A6xG pin definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	WLCSP100	WLCSP100_SMPS	LQFP100	UFBGA132	UFBGA132_SMPS	LQFP144	LQFP144_SMPS	UFBGA169	UFBGA169_SMPS					Alternate functions	Additional functions
38	F3	E4	64	E11	E11	97	97	G12	G12	PC7	I/O	FT_l	-	TIM3_CH2, TIM8_CH2, DFSDM1_DATIN3, TSC_G4_IO2, DCMI_D1, LCD_SEG25, SDMMC1_D7, SAI2_MCLK_B, EVENTOUT	-
39	E1	E1	65	E10	E10	98	98	G10	G10	PC8	I/O	FT_l	-	TIM3_CH3, TIM8_CH3, TSC_G4_IO3, DCMI_D2, LCD_SEG26, SDMMC1_D0, EVENTOUT	-
40	E2	E2	66	D12	D12	99	99	G9	G9	PC9	I/O	FT_fl	-	TIM8_BKIN2, TIM3_CH4, TIM8_CH4, DCMI_D3, I2C3_SDA, TSC_G4_IO4, OTG_FS_NOE, LCD_SEG27, SDMMC1_D1, SAI2_EXTCLK, TIM8_BKIN2_COMP1, EVENTOUT	-
41	E3	E3	67	D11	D11	100	100	G8	G8	PA8	I/O	FT_l	-	MCO, TIM1_CH1, USART1_CK, OTG_FS_SOF, LCD_COM0, SWPMI1_IO, SAI1_SCK_A, LPTIM2_OUT, EVENTOUT	-
42	D3	D3	68	D10	D10	101	101	F10	F10	PA9	I/O	FT_lu	-	TIM1_CH2, SPI2_SCK, DCMI_D0, USART1_TX, LCD_COM1, SAI1_FS_A, TIM15_BKIN, EVENTOUT	OTG_FS_VBUS
43	D2	D2	69	C12	C12	102	102	F9	F9	PA10	I/O	FT_lu	-	TIM1_CH3, DCMI_D1, USART1_RX, OTG_FS_ID, LCD_COM2, SAI1_SD_A, TIM17_BKIN, EVENTOUT	-

Table 17. Alternate function AF8 to AF15[1] (continued)

Port		AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		UART4/5/ LPUART1/ CAN2	CAN1/TSC	CAN2/ OTG_FS/DCMI/ QUADSPI	LCD	SDMMC/ COMP1/2/FMC/SWPMI1	SAI1/2	TIM2/15/16/17/ LPTIM2	EVENOUT
Port B	PB0	-	-	QUADSPI_BK1_IO1	LCD_SEG5	COMP1_OUT	SAI1_EXTCLK	-	EVENTOUT
	PB1	LPUART1_RTS_DE	-	QUADSPI_BK1_IO0	LCD_SEG6	-	-	LPTIM2_IN1	EVENTOUT
	PB2	-	-	-	LCD_VLCD	-	-	-	EVENTOUT
	PB3	-	-	OTG_FS_CRS_SYNC	LCD_SEG7	-	SAI1_SCK_B	-	EVENTOUT
	PB4	UART5_RTS_DE	TSC_G2_IO1	DCMI_D12	LCD_SEG8	-	SAI1_MCLK_B	TIM17_BKIN	EVENTOUT
	PB5	UART5_CTS	TSC_G2_IO2	DCMI_D10	LCD_SEG9	COMP2_OUT	SAI1_SD_B	TIM16_BKIN	EVENTOUT
	PB6	CAN2_TX	TSC_G2_IO3	DCMI_D5	-	TIM8_BKIN2_COMP2	SAI1_FS_B	TIM16_CH1N	EVENTOUT
	PB7	UART4_CTS	TSC_G2_IO4	DCMI_VSYNC	LCD_SEG21	FMC_NL	TIM8_BKIN_COMP1	TIM17_CH1N	EVENTOUT
	PB8	-	CAN1_RX	DCMI_D6	LCD_SEG16	SDMMC1_D4	SAI1_MCLK_A	TIM16_CH1	EVENTOUT
	PB9	-	CAN1_TX	DCMI_D7	LCD_COM3	SDMMC1_D5	SAI1_FS_A	TIM17_CH1	EVENTOUT
	PB10	LPUART1_RX	TSC_SYNC	QUADSPI_CLK	LCD_SEG10	COMP1_OUT	SAI1_SCK_A	-	EVENTOUT
	PB11	LPUART1_TX	-	QUADSPI_BK1_NCS	LCD_SEG11	COMP2_OUT	-	-	EVENTOUT
	PB12	LPUART1_RTS_DE	TSC_G1_IO1	CAN2_RX	LCD_SEG12	SWPMI1_IO	SAI2_FS_A	TIM15_BKIN	EVENTOUT
	PB13	LPUART1_CTS	TSC_G1_IO2	CAN2_TX	LCD_SEG13	SWPMI1_TX	SAI2_SCK_A	TIM15_CH1N	EVENTOUT
	PB14	-	TSC_G1_IO3	-	LCD_SEG14	SWPMI1_RX	SAI2_MCLK_A	TIM15_CH1	EVENTOUT
	PB15	-	TSC_G1_IO4	-	LCD_SEG15	SWPMI1_SUSPEND	SAI2_SD_A	TIM15_CH2	EVENTOUT

Table 34. Typical current consumption in Run, with different codes running from Flash, ART enable (Cache ON Prefetch OFF) and power supplied (by external SMPS (V_{DD12} = 1.05 V)

Symbol	Parameter	Conditions(1)			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	f_{HCLK} = f_{HSE} up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	f_{HCLK} = 26 MHz	Reduced code(2)	1.04	mA	40	µA/MHz
				Coremark	1.17		45	
				Dhrystone 2.1	1.22		47	
				Fibonacci	1.14		44	
				While(1)	0.96		37	

1. All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V_{DD12} = 1.05 V
2. Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 35. Typical current consumption in Run and Low-power run modes, with different codes running from Flash, ART disable

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	f_{HCLK} = f_{HSE} up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	3.1	mA	119	µA/MHz
				Coremark	2.85		110	
				Dhrystone 2.1	2.86		110	
				Fibonacci	2.63		101	
				While(1)	2.42		93.1	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	10	mA	125	µA/MHz
				Coremark	9.33		117	
				Dhrystone 2.1	9.4		118	
				Fibonacci	8.66		108	
				While(1)	8.61		108	
I_{DD_ALL} (LPRun)	Supply current in Low-power run	f_{HCLK} = f_{MSI} = 2 MHz all peripherals disable		Reduced code(1)	378	µA	189	µA/MHz
				Coremark	412		206	
				Dhrystone 2.1	418		209	
				Fibonacci	392		196	
				While(1)	266		133	

1. Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 38. Typical current consumption in Run and Low-power run modes, with different codes running from SRAM1

Symbol	Parameter	Conditions			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2 f_{HCLK} = 26 MHz	Reduced code(1)	2.72	mA	105	µA/MHz
				Coremark	2.72		105	
				Dhrystone 2.1	2.65		102	
				Fibonacci	2.47		95	
				While(1)	2.37		91	
			Range 1 f_{HCLK} = 80 MHz	Reduced code(1)	9.71	mA	121	µA/MHz
				Coremark	9.7		121	
				Dhrystone 2.1	9.48		119	
				Fibonacci	8.79		110	
				While(1)	8.45		106	
I_{DD_ALL} (LPRun)	Supply current in Low-power run	$f_{HCLK} = f_{MSI}$ = 2 MHz all peripherals disable		Reduced code(1)	258	µA	129	µA/MHz
				Coremark	268		134	
				Dhrystone 2.1	240		120	
				Fibonacci	230		115	
				While(1)	255		128	

1. Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 39. Typical current consumption in Run, with different codesrunning from SRAM1 and power supplied by external SMPS (V_{DD12} = 1.10 V)

Symbol	Parameter	Conditions(1)			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	$f_{HCLK} = f_{HSE}$ up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	f_{HCLK} = 26 MHz	Reduced code(2)	1.17	mA	45	µA/MHz
				Coremark	1.17		45	
				Dhrystone 2.1	1.14		44	
				Fibonacci	1.07		41	
				While(1)	1.02		39	
			f_{HCLK} = 80 MHz	Reduced code(1)	3.49		44	
				Coremark	3.49		44	
				Dhrystone 2.1	3.41		43	
				Fibonacci	3.16		39	
				While(1)	3.04		38	

1. All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V_{DD12} = 1.10 V
2. Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 40. Typical current consumption in Run, with different codesrunning from SRAM1 and power supplied by external SMPS (V_{DD12} = 1.05 V)

Symbol	Parameter	Conditions(1)			TYP	Unit	TYP	Unit
		-	Voltage scaling	Code	25 °C		25 °C	
I_{DD_ALL} (Run)	Supply current in Run mode	f_{HCLK} = f_{HSE} up to 48 MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	f_{HCLK} = 26 MHz	Reduced code(2)	1.07	mA	41	µA/MHz
				Coremark	1.07		41	
				Dhrystone 2.1	1.04		40	
				Fibonacci	0.97		37	
				While(1)	0.93		36	

1. All values are obtained by calculation based on measurements done without SMPS and using following parameters: SMPS input = 3.3 V, SMPS efficiency = 85%, V_{DD12} = 1.05 V
2. Reduced code used for characterization results provided in *Table 26*, *Table 28*, *Table 30*.

Table 43. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX(1)					Unit
		-	Voltage scaling	f_{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (LPSleep)	Supply current in low-power sleep mode	$f_{HCLK} = f_{MSI}$ all peripherals disable		2 MHz	92.7	124	258	487	968	105	224	474	969	2006	µA
				1 MHz	63.5	97.5	223	460	951	75	193	446	942	1975	
				400 kHz	42.6	75.6	207	443	947	54	171	426	923	1955	
				100 kHz	31.2	67.6	199	437	905	44	162	420	916	1947	

1. Guaranteed by characterization results, unless otherwise specified.

Table 44. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX(1)					Unit
		-	V_{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I_{DD_ALL} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	LCD disabled	1.8 V	2.57	6.86	25.2	60.1	135	5.3	16.4	64	154.6	353	µA
			2.4 V	2.62	6.91	25.5	60.6	137	5.3	16.6	64.9	156.7	359	
			3 V	2.69	6.93	25.7	61.5	140	5.4	16.9	66.3	159.7	366	
			3.6 V	2.7	7.08	26.3	62.9	143	5.4	17.4	67.8	163.8	375	
		LCD enabled(2) clocked by LSI	1.8 V	2.92	7.19	25.3	59.5	135	5.3	16.6	64.8	155.6	355	
			2.4 V	2.99	7.3	25.6	60.3	136	5.5	16.8	65.9	157.9	360	
			3 V	3.04	7.41	26.1	61.7	140	5.9	17.3	67.1	160.8	367	
			3.6 V	3.31	7.7	26.8	63.2	143	6.2	17.9	69.1	165.0	376	

6.3.9 PLL characteristics

The parameters given in *Table 62* are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in *Table 22: General operating conditions*.

Table 62. PLL, PLLSAI1, PLLSAI2 characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock(2)	-	4	-	16	MHz
	PLL input clock duty cycle	-	45	-	55	%
$f_{PLL\_P\_OUT}$	PLL multiplier output clock P	Voltage scaling Range 1	2.0645	-	80	MHz
		Voltage scaling Range 2	2.0645	-	26	
$f_{PLL\_Q\_OUT}$	PLL multiplier output clock Q	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	
$f_{PLL\_R\_OUT}$	PLL multiplier output clock R	Voltage scaling Range 1	8	-	80	MHz
		Voltage scaling Range 2	8	-	26	
f_{VCO_OUT}	PLL VCO output	Voltage scaling Range 1	64	-	344	MHz
		Voltage scaling Range 2	64	-	128	
t_{LOCK}	PLL lock time	-	-	15	40	µs
Jitter	RMS cycle-to-cycle jitter	System clock 80 MHz	-	40	-	±ps
	RMS period jitter		-	30	-	
I_{DD}(PLL)	PLL power consumption on V_{DD}(1)	VCO freq = 64 MHz	-	150	200	µA
		VCO freq = 96 MHz	-	200	260	
		VCO freq = 192 MHz	-	300	380	
		VCO freq = 344 MHz	-	520	650	

1. Guaranteed by design.
2. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the 3 PLLs.

6.3.10 Flash memory characteristics

Table 63. Flash memory characteristics(1)

Symbol	Parameter	Conditions	Typ	Max	Unit
t_{prog}	64-bit programming time	-	81.69	90.76	µs
t_{prog_row}	one row (32 double word) programming time	normal programming	2.61	2.90	ms
		fast programming	1.91	2.12	
t_{prog_page}	one page (2 Kbyte) programming time	normal programming	20.91	23.24	
		fast programming	15.29	16.98	
t_{ERASE}	Page (2 KB) erase time	-	22.02	24.47	
t_{prog_bank}	one bank (512 Kbyte) programming time	normal programming	5.35	5.95	s
		fast programming	3.91	4.35	

Table 72. I/O AC characteristics(1)(2)

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	5	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	10	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	1.5	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	52	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	140	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	17	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	37	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	25	MHz
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	10	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	50	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	15	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	9	ns
			C=50 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	16	
			C=50 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	40	
			C=10 pF, 2.7 V≤V_{DDIOx}≤3.6 V	-	4.5	
			C=10 pF, 1.62 V≤V_{DDIOx}≤2.7 V	-	9	
			C=10 pF, 1.08 V≤V_{DDIOx}≤1.62 V	-	21	

2. The I/O analog switch voltage booster is enable when V_{DDA} < 2.4 V (BOOSTEN = 1 in the SYSCFG_CFGR1 when V_{DDA} < 2.4V). It is disable when V_{DDA} ≥ 2.4 V.
3. Fast channels are: PC0, PC1, PC2, PC3, PA0.
4. Slow channels are: all ADC inputs except the fast channels.

Table 86. OPAMP characteristics(1) (continued)

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
GM	Gain margin	Normal mode		-	13	-	dB
		Low-power mode		-	20	-	
t_{WAKEUP}	Wake up time from OFF state.	Normal mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 4 kΩ follower configuration	-	5	10	µs
		Low-power mode	C_{LOAD} ≤ 50 pf, R_{LOAD} ≥ 20 kΩ follower configuration	-	10	30	
I_{bias}	OPAMP input bias current	General purpose input (all packages except UFBGA132 and UFBGA169 only)		-	-	(3)	nA
		Dedicated input (UFBGA132 and UFBGA169 only)	T_J ≤ 75 °C	-	-	1	
			T_J ≤ 85 °C	-	-	3	
			T_J ≤ 105 °C	-	-	8	
			T_J ≤ 125 °C	-	-	15	
PGA gain(2)	Non inverting gain value	-		-	2	-	-
				-	4	-	
				-	8	-	
				-	16	-	
$R_{network}$	R2/R1 internal resistance values in PGA mode(4)	PGA Gain = 2		-	80/80	-	kΩ/kΩ
		PGA Gain = 4		-	120/ 40	-	
		PGA Gain = 8		-	140/ 20	-	
		PGA Gain = 16		-	150/ 10	-	
Delta R	Resistance variation (R1 or R2)	-		-15	-	15	%
PGA gain error	PGA gain error	-		-1	-	1	%
PGA BW	PGA bandwidth for different non inverting gain	Gain = 2	-	-	GBW/ 2	-	MHz
		Gain = 4	-	-	GBW/ 4	-	
		Gain = 8	-	-	GBW/ 8	-	
		Gain = 16	-	-	GBW/ 16	-	

Figure 39. Quad SPI timing diagram - SDR mode

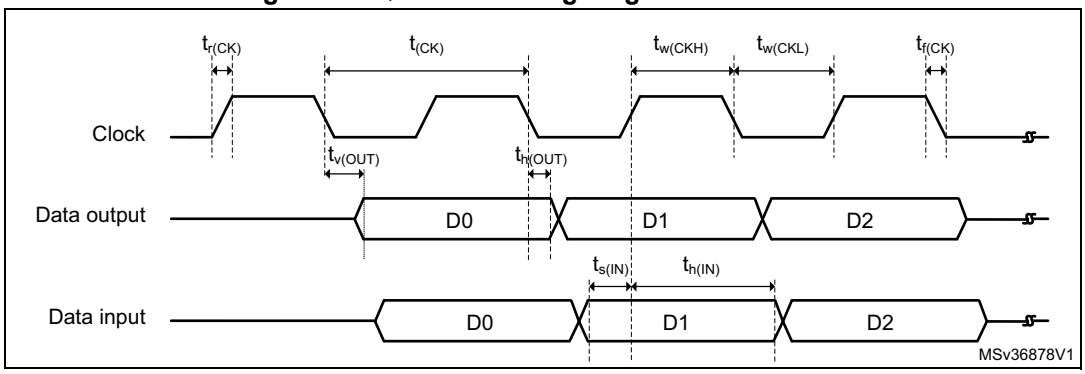
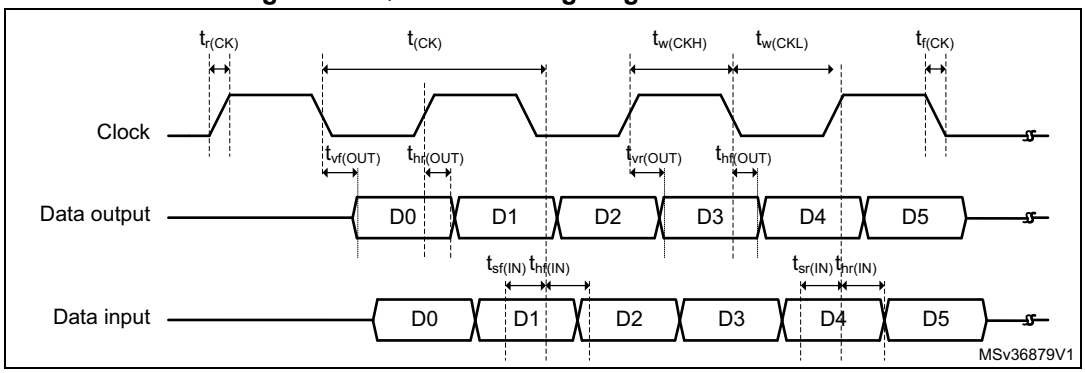
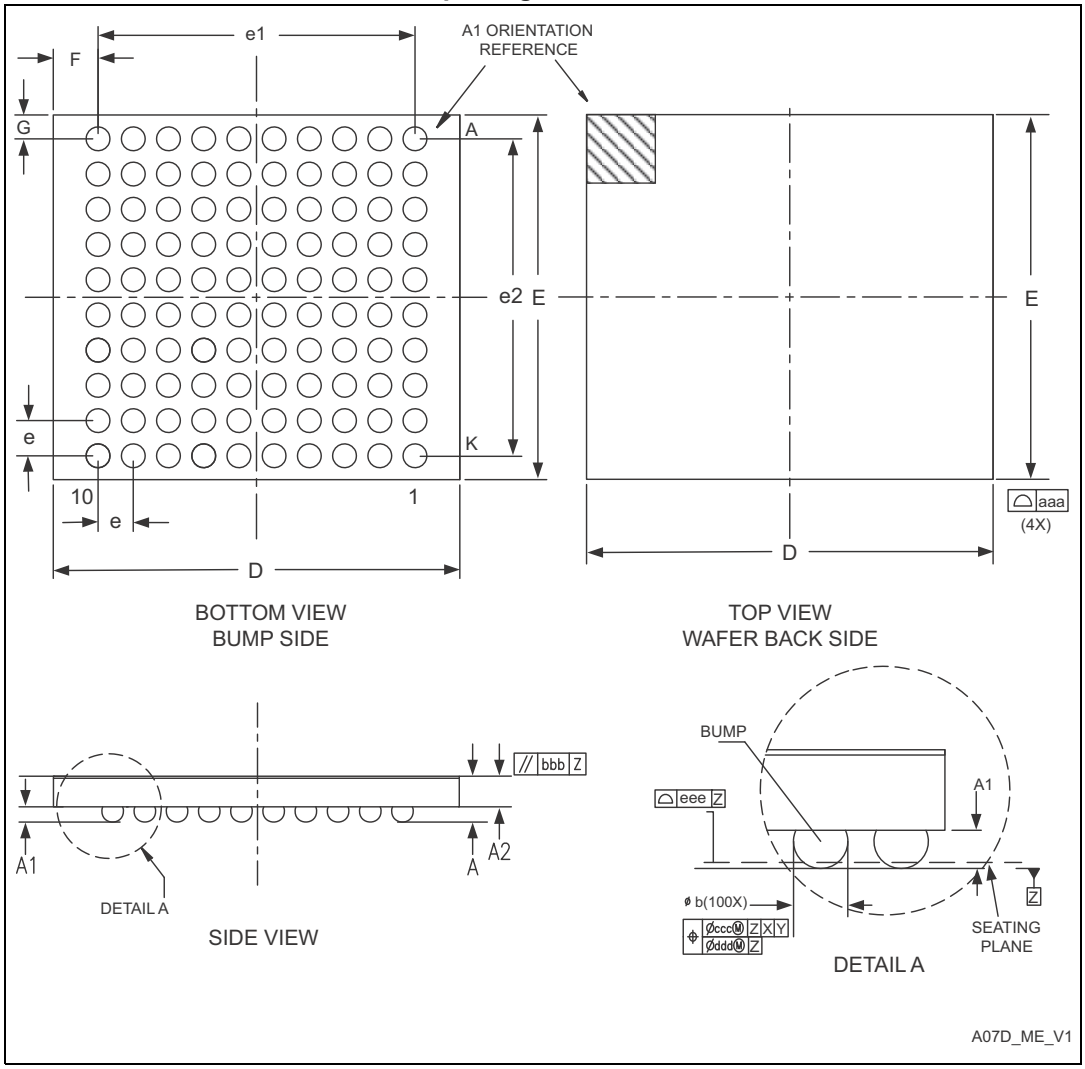


Figure 40. Quad SPI timing diagram - DDR mode



7.5 WLCSP100 package information

Figure 76.WLCSP – 100 ball, 4.618 x 4.142 mm, 0.4 mm pitch wafer level chip scale package outline



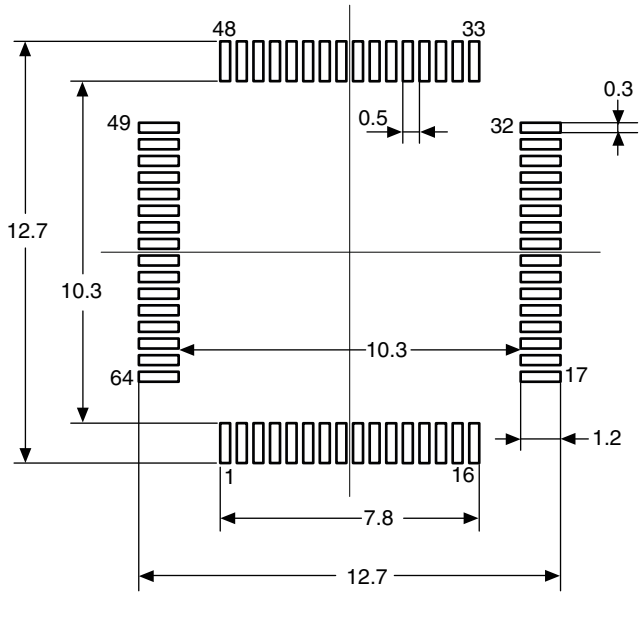
1. Drawing is not to scale.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.
3. Primary datum Z and seating plane are defined by the spherical crowns of the bump.
4. Bump position designation per JESD 95-1, SPP-010.

Table 131. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 81. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax} = 175 + 272 = 447 mW

Using the values obtained in *Table 132* T_{Jmax} is calculated as follows:

– For LQFP100, 42 °C/W

T_{Jmax} = 82 °C + (42 °C/W × 447 mW) = 82 °C + 18.774 °C = 100.774 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C) see *Section 8: Ordering information*.

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 3).

Suffix 6: T_{Amax} = T_{Jmax} - (42°C/W × 447 mW) = 105-18.774 = 86.226 °C

Suffix 3: T_{Amax} = T_{Jmax} - (42°C/W × 447 mW) = 130-18.774 = 111.226 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax} = 100 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

Using the values obtained in *Table 132* T_{Jmax} is calculated as follows:

– For LQFP100, 42 °C/W

T_{Jmax} = 100 °C + (42 °C/W × 134 mW) = 100 °C + 5.628 °C = 105.628 °C

This is above the range of the suffix 6 version parts (–40 < T_J < 105 °C).